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				Application Number	National Stage of PCT/JP2004/014128 <i>10/572680</i>
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				First Named Inventor	Hideki TOMOZAWA
				Art Unit	Unknown 2818
				Examiner Name	HOANG QUAN HO
Sheet	1	of	1	Attorney Docket Number	Q77727

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US			
		US			

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Translation ⁴
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)		
HQH		JP	10-209500	A	08/07/1998 TOYODA GOSEI CO. LTD	Abstract
HQH		JP	10-135515	A	05/22/1998 TOYODA GOSEI CO., LTD. and TOYOTA CENTRAL RES. & DEV. LAB INC.	Abstract
HQH		JP	10-308534	A	11/17/1998 SHOWA DENKO KK	Abstract

NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.			Translation ⁶
HQH		LI-CHIEN CHEN, ET AL "MICROSTRUCTURAL INVESTIGATION OF OXIDIZED Ni/Au OHMIC CONTACT TO p-type GaN", JOURNAL OF APPLIED PHYSICS, Vol. 86, No. 7, October 1, 1999, pages 3826-3832			
		JIN-KUO HO, ET AL "LOW-RESISTANCE OHMIC CONTACTS TO p-type GaN ACHIEVED BY THE OXIDATION OF Ni/Au FILMS", JOURNAL OF APPLIED PHYSICS, Vol. 86, No. 8, October 15, 1999, pages 4491-4497			
		LI-CHIEN CHEN, "OXIDIZED Ni/Pt AND Ni/Au OHMIC CONTACTS TO p-type GaN", APPLIED PHYSICS LETTERS, Vol. 76, No. 25, June 19, 2000, pages 3703-3705			
		D. QIAO, ET AL, "A STUDY OF THE Au/Ni OHMIC CONTACT ON p-GaN", JOURNAL OF APPLIED PHYSICS, Vol. 88, No. 7, October 1, 2000, pages 4196-4200			
		J. NARAYAN, ET AL, "FORMATION OF EPITAXIAL Au/Ni/Au OHMIC CONTACTS TO p-GaN", APPLIED PHYSICS LETTERS, Vol. 81, No. 21, November 18, 2002, pages 3978-3980			
		HO WON JANG, ET AL, "MECHANISM FOR OHMIC CONTACT FORMATION OF OXIDIZED Ni/Au ON p-type GaN", JOURNAL OF APPLIED PHYSICS, Vol. 94, No. 3, August 1, 2003, pages 1748-1752			
		D. MISTELE, ET AL, "INVESTIGATION OF Ni/Au CONTACTS ON p-GaN ANNEALED IN DIFFERENT ATMOSPHERES", JOURNAL OF CRYSTAL GROWTH, Vol. 230, No. 1/2, 2001, pages 564-568			
		B. LIU, ET AL, "EFFECTS OF A Ni CAP LAYER ON TRANSPARENT Ni/Au OHMIC CONTACTS TO p-GaN", J. VAC. SCI. TECHNOL. B, Vol. 20, No. 4, Jul/Aug 2002, pages 1394-1401			
HQH		J. K. SHEU, ET AL, "THE EFFECT OF THERMAL ANNEALING ON THE Ni/Au CONTACT OF p-type GaN", JOURNAL OF APPLIED PHYSICS, Vol. 83, No. 6, March 15, 1998, pages 3172-3175			

Examiner Signature	/Hoang Quan Ho/	Date Considered	02/02/2007
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